AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph [0010] at page 2, with the following rewritten paragraph:

-- The invention meets the objects by providing a method of selective etching comprising:

- providing a first material selected from a group A on a substrate
- providing a second material selected from a group B on a substrate
- selectively etching said first material with a selectivity of at least 2:1 towards said second material by a liquid etchant flowing across the substrate surface at a flow sufficient fast to generate a mean velocity v parallel to the substrate's surface of minimum ~~0,1m/s~~ 0.1 m/s. A preferred velocity v is above ~~0,5~~ 0.5 m/s. --

Please replace the paragraph [0013] at page 3, with the following rewritten paragraph:

--For a given cross sectional area (a) of the gap the necessary volume flow (Q) can be selected to achieve the minimum velocity. For instance a substrate diameter of ~~0,2~~ 0.2 m(e.g. a 200 mm wafer) and a gap distance d = 1 mm leads to a minimum volume flow of 2E-5 m^3/s (= ~~1,2~~ 1.2 l/min).--

Please replace the paragraph [0027] at page 4, with the following rewritten paragraph:

--Although the velocity is not primarily depending on the volume flow a minimum flow is useful in order to evenly cover the substrate when liquid is dispensed on it. A volume flow of at least ~~0,05~~ 0.05 l/min (especially at least ~~0,5~~ 0.5 l/min) is preferred.--

Please replace the paragraph [0041] at page 6, with the following rewritten paragraph:

--As can be seen on the chart of Fig. 2, etch rate of HfO_2 and ThOx decreases when using a high flow across the substrate. Whereas the etch rate of annealed and pretreated HfO_2 decreases only by a factor ~~1,3~~ 1.3 the etch rate of ThOx decreases by a factor 9. The etch rate of HfO_2 even just as deposited decreased only by a factor ~~3,5~~ 3.5. Hence the etch selectivity of HfO_2 (annealed and pretreated) towards ThOx increased from 12:1 to 88:1. This improvement of selectivity of a factor 7 is extraordinary, when keeping temperature and composition of the etchant unchanged.--

Please replace the paragraph [0041] at page 6, with the following rewritten paragraph:

--In another embodiment a mixture of water, HCl ~~(2,4mol/l)~~ (2.4mol/l) and HF ~~(0,05mol/l)~~ (0.05mol/l) was used, again at 55°C. The chart in Fig. 3 shows again a decrease of the

etch rate of HfO_2 and ThOx when using a high flow across the substrate. The etch selectivity of HfO_2 (annealed and pretreated) towards ThOx increased from 18:1 (immersed in an etching bath) to 93:1 (using a high flow across the substrate in a spin processor).--